

EVVOSEMI[®]

THINK CHANGE DO



ESD



TVS



MOS



LDO



Diode



Sensor



DC-DC

Product Specification

▶ Domestic	Part Number	EV2SC4672-SB
▶ Overseas	Part Number	2SC4672
▶ Equivalent	Part Number	2SC4672

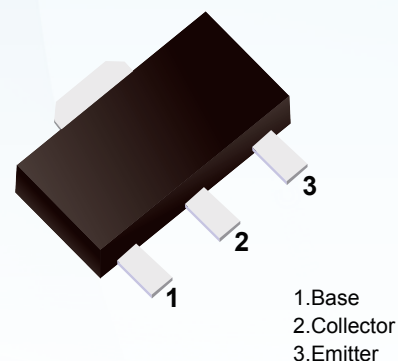
"SB" means SOT-89

EV is the abbreviation of name EVVO

■ NPN Transistors

■ Features

- Low Saturation Voltage
- Excellent h_{FE} Characteristics
- Complementary to 2SA1797



■ Simplified outline(SOT-89)

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	60	V
Collector - Emitter Voltage	V_{CE0}	50	
Emitter - Base Voltage	V_{EB0}	6	
Collector Current - Continuous	I_C	2	A
Collector Power Dissipation	P_C	500	mW
Thermal Resistance From Junction To Ambient	$R_{\theta JA}$	250	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to 150	

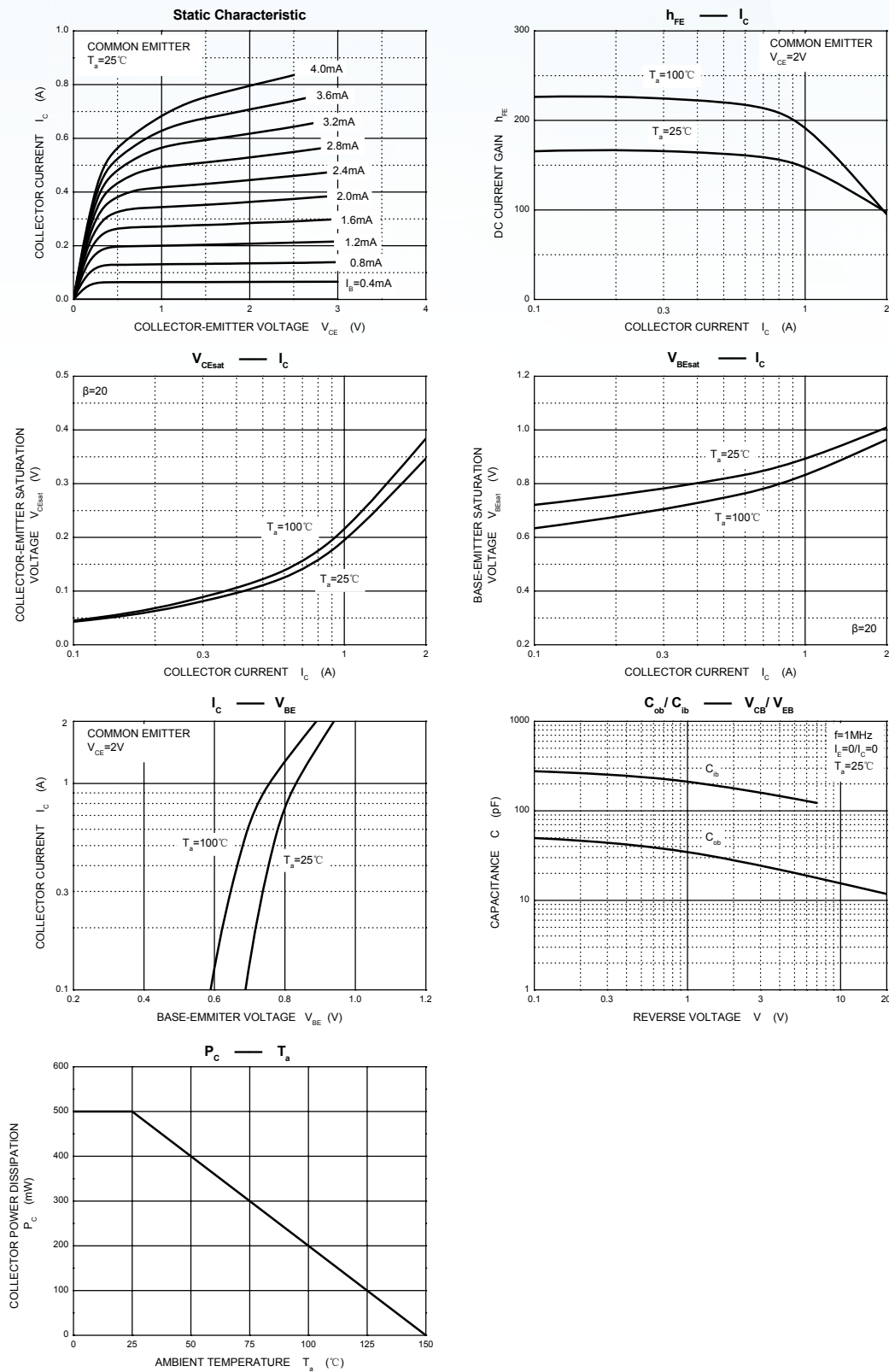
■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_C = 50 \mu\text{A}, I_E = 0$	60			V
Collector- emitter breakdown voltage	V_{CE0}	$I_C = 1 \text{ mA}, I_B = 0$	50			
Emitter - base breakdown voltage	V_{EB0}	$I_E = 50 \mu\text{A}, I_C = 0$	6			
Collector-base cut-off current	I_{CB0}	$V_{CB} = 60\text{V}, I_E = 0$			0.1	μA
Emitter cut-off current	I_{EB0}	$V_{EB} = 5\text{V}, I_C = 0$			0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 1\text{A}, I_B = 50\text{mA}$			0.35	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = 1\text{A}, I_B = 50\text{mA}$			1.2	
DC current gain	h_{FE}	$V_{CE} = 2\text{V}, I_C = 500\text{mA}$	82		390	
Collector output capacitance	C_{ob}	$V_{CB} = 10\text{V}, I_E = 0, f = 1\text{MHz}$		25		pF
Transition frequency	f_T	$V_{CE} = 2\text{V}, I_C = 500\text{mA}, f = 100\text{MHz}$		210		MHz

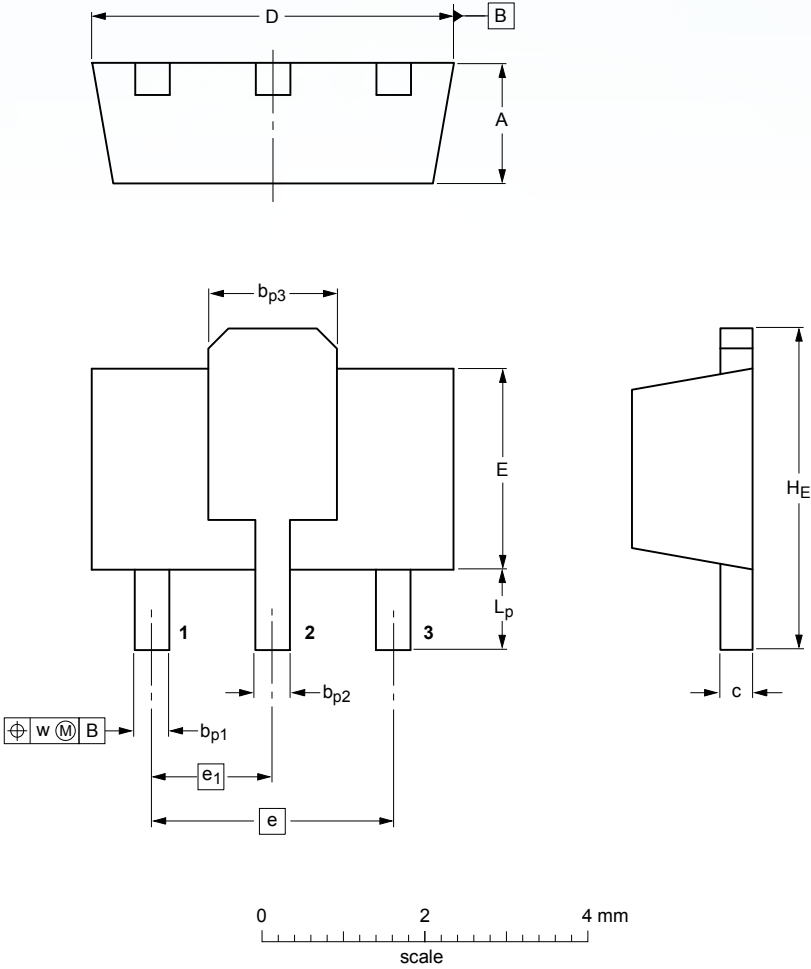
■ Classification of h_{FE}

Type	2SC4672-P	2SC4672-Q	2SC4672-R
Range	82-180	120-270	180-390
Marking	DKP	DKQ	DKR

■ Typical Characteristics



■ SOT-89



DIMENSIONS (mm are the original dimensions)

UNIT	A	b _{p1}	b _{p2}	b _{p3}	c	D	E	e	e ₁	H _E	L _p	w
mm	1.6 1.4	0.48 0.35	0.53 0.40	1.8 1.4	0.44 0.23	4.6 4.4	2.6 2.4	3.0	1.5	4.25 3.75	1.2 0.8	0.13

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